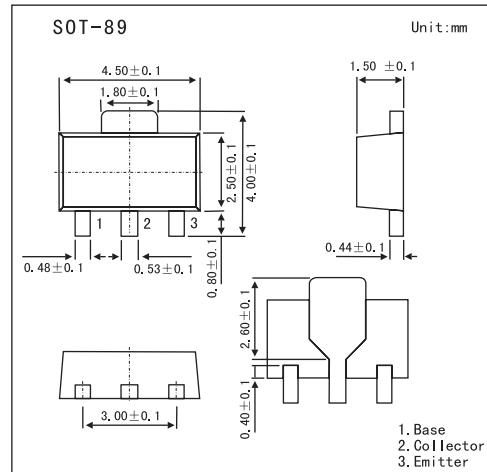


PNP Epitaxial Planar Silicon Transistors

2SB1397

■ Features

- Low saturation voltage.
- Contains diode between collector and emitter.
- Contains bias resistance between base and emitter.
- Large current capacity.
- Small-sized package making it easy to provide high density, small-sized hybrid ICs.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	-25	V
Collector-emitter voltage	V _{CEO}	-20	V
Emitter-base voltage	V _{EBO}	-6	V
Collector current	I _C	-2	A
Collector current (pulse)	I _{CP}	-4	A
Collector dissipation	P _C *	1.3	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

* Mounted on ceramic board (250mm² × 0.8mm)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I _{CBO}	V _{CB} = -20V , I _E = 0			-1	nA
DC current Gain	h _{FE}	V _{CE} = -2V , I _C = -0.5A	70			
		V _{CE} = -2V , I _C = -2A	50			
Gain bandwidth product	f _T	V _{CE} = -2V , I _C = -0.5A		300		MHz
Output capacitance	C _{ob}	V _{CB} = -10V , f = 1MHz		40		pF
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -1A , I _B = -50mA		-0.25	-0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = -1A , I _B = -50mA			-1.5	V
Collector-to-base breakdown voltage	V _{(BR)CBO}	I _C = -10μA , I _E = 0	-25			V
Collector-to-emitter breakdown voltage	V _{(BR)CEO1}	I _C = -10μA , R _{BE} = ∞	-25			V
Collector-to-emitter breakdown voltage	V _{(BR)CEO2}	I _C = -10mA , R _{BE} = ∞	-20			
Diode forward voltage	V _F	I _F =0.5A			-1.5	V
Base-emitter resistance	R _{BE}			1.6		kΩ

■ Marking

Marking	BP
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